

**isc Silicon PNP Darlington Power Transistor**
**2SB1411**
**DESCRIPTION**

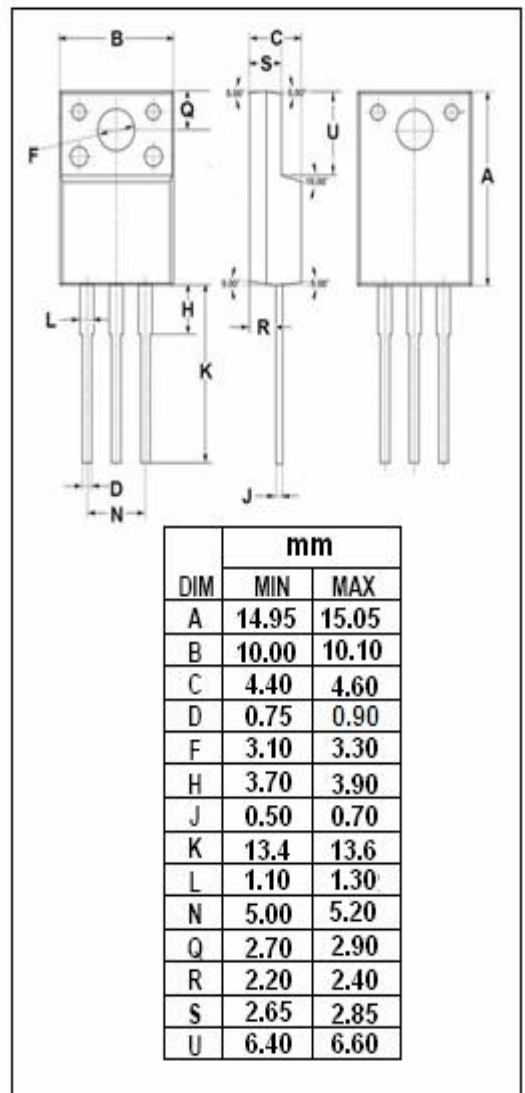
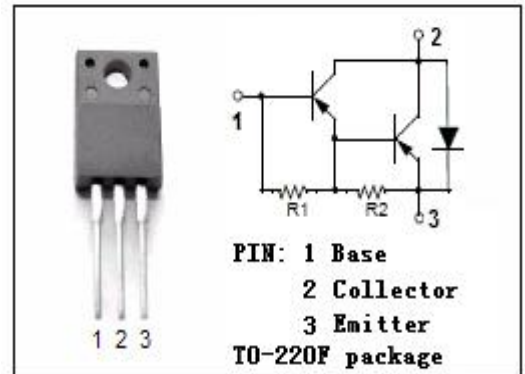
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -100V(\text{Min})$
- High DC Current Gain-  
:  $h_{FE} = 1500(\text{Min})@ (V_{CE} = -3V, I_C = -1A)$
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = -1.5V(\text{Max})@ (I_C = -1A, I_B = -2mA)$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- High power switching applications.
- Hammer drive, pulse motor drive applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-100	V
$V_{EBO}$	Emitter-Base Voltage	-7	V
$I_C$	Collector Current-Continuous	-2	A
$I_{CM}$	Collector Current-Peak	-3	A
$I_B$	Base Current-Continuous	-0.5	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



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**ELECTRICAL CHARACTERISTICS**
**T<sub>j</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-100			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -2mA			-1.5	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -8mA			-2.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -2mA			-2.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -6V; I <sub>C</sub> = 0			-2.5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -3V	1500		15000	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> = -3V	1000			

**Switching Times**

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = -1A, I <sub>B1</sub> = -I <sub>B2</sub> = -2mA, V <sub>CC</sub> ≈ -30V; R <sub>L</sub> = 30 Ω		1.0		μ s
t <sub>stg</sub>	Storage Time			3.0		μ s
t <sub>f</sub>	Fall Time			2.0		μ s

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